

ABSTRACT

Single crystal silicon and a silicon wafer with a controllable oxygen content, a single crystal silicon growth method and system are provided. The method includes: obtaining an actual heating duration of a quartz crucible during the growth of single crystal silicon; determining a control parameter set and a configuration parameter value of the control parameter set based on a difference range in which a difference between the actual heating duration and a target heating duration lies, the control parameter set including a silicon rotation speed and/or a crucible rotation speed, and various control parameter sets corresponding to distinct difference ranges; and automatically configuring a corresponding control parameter based on the configuration parameter value of the control parameter set to allow an oxygen content deviation between an oxygen content of the single crystal silicon and a target oxygen content to be -10% to 10%.

(Figure 3)